

Silicon PNP Power Transistors

TIP30/30A/30B/30C

DESCRIPTION

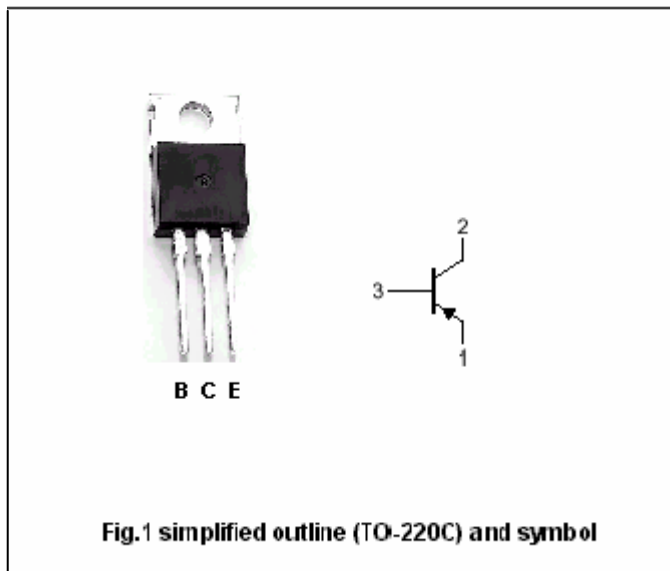
- With TO-220C package
- Complement to type TIP29/29A/29B/29C

APPLICATIONS

- For use in general purpose power amplifier and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	TIP30	-40	V
		TIP30A	-60	
		TIP30B	-80	
		TIP30C	-100	
V _{CEO}	Collector-emitter voltage	TIP30	-40	V
		TIP30A	-60	
		TIP30B	-80	
		TIP30C	-100	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current (DC)		-1	A
I _{CM}	Collector current-Pulse		-3	A
I _B	Base current		-0.4	A
P _C	Collector power dissipation	T _C =25	30	w
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CEO(SUS)}	Collector-emitter sustaining voltage	TIP30	-40			V	
		TIP30A	-60				
		TIP30B	-80				
		TIP30C	-100				
		I _C =-30mA; I _B =0					
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.125A			-0.7	V	
V _{BE}	Base-emitter on voltage	I _C =-1A; V _{CE} =-4V			-1.3	V	
I _{CES}	Collector cut-off current	TIP30	V _{CE} =-40V; V _{EB} =0			-0.2	mA
		TIP30A	V _{CE} =-60V; V _{EB} =0				
		TIP30B	V _{CE} =-80V; V _{EB} =0				
		TIP30C	V _{CE} =-100V; V _{EB} =0				
I _{CEO}	Collector cut-off current	TIP30/30A	V _{CE} =-30V; I _B =0			-0.3	mA
		TIP30B/30C	V _{CE} =-60V; I _B =0				
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1.0	mA	
h _{FE-1}	DC current gain	I _C =-0.2A; V _{CE} =-4V	40				
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-4V	15		75		
f _T	Transiton frequency	I _C =-0.2A; V _{CE} =-10V; f=1MHz	3			MHz	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	4.167	/W

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PACKAGE OUTLINE

